

**Trench™  
Power MOSFET**

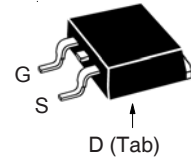
**IXTA32N20T  
IXTP32N20T**

**V<sub>DSS</sub> = 200V**  
**I<sub>D25</sub> = 32A**  
**R<sub>DS(on)</sub> ≤ 78mΩ**

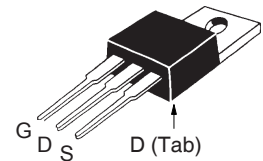
N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Rectifier



TO-263 AA (IXTA)



TO-220AB (IXTP)



G = Gate      D = Drain  
 S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 175°C	200	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 175°C, R <sub>GS</sub> = 1MΩ	200	V
V <sub>GSS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	32	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, Pulse Width Limited by T <sub>JM</sub>	64	A
I <sub>A</sub>	T <sub>C</sub> = 25°C	16	A
E <sub>AS</sub>	T <sub>C</sub> = 25°C	250	mJ
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 175°C	10	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	200	W
T <sub>J</sub>		- 55 ... +175	°C
T <sub>JM</sub>		175	°C
T <sub>stg</sub>		- 55 ... +175	°C
T <sub>L</sub>	1.6mm (0.062in.) from Case for 10s	300	°C
T <sub>sold</sub>	Plastic Body for 10 Seconds	260	°C
M <sub>d</sub>	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g

Symbol	Test Conditions (T <sub>J</sub> = 25°C Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	200		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	3.0		5.0 V
I <sub>GSS</sub>	V <sub>GS</sub> = ± 20V, V <sub>DS</sub> = 0V			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0V T <sub>J</sub> = 150°C			3 μA 200 μA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Notes 1, 2			78 mΩ

**Features**

- International Standard Packages
- 175°C Operating Temperature
- Avalanche Rated
- Low R<sub>DS(on)</sub>
- Fast Intrinsic Rectifier
- High Current Handling Capability

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	18	30	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		1760	pF
$C_{oss}$			212	pF
$C_{rss}$			31	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 15\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		14	ns
$t_r$			18	ns
$t_{d(off)}$			55	ns
$t_f$			31	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		38	nC
$Q_{gs}$			12	nC
$Q_{gd}$			13	nC
$R_{thJC}$	TO-220		0.50	$^\circ\text{C}/\text{W}$
$R_{thCH}$				$^\circ\text{C}/\text{W}$

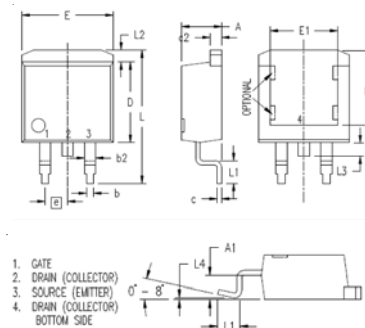
### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
$I_S$	$V_{GS} = 0\text{V}$			32 A	
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			128 A	
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.2 V	
$t_{rr}$	$I_F = 0.5 \cdot I_{D25}$ , $V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 0.5 \cdot V_{DSS}$		110	ns	
$I_{RM}$				6.90	A
$Q_{RM}$				0.38	nC

### Notes:

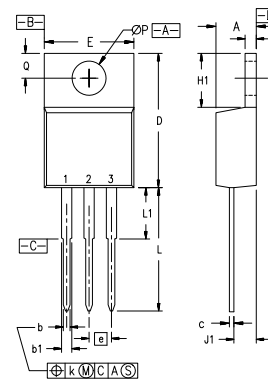
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. On through-hole packages,  $R_{DS(on)}$  Kelvin test contact location must be 5mm or less from the package body.

### TO-263 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

### TO-220 Outline



Pins: 1 - Gate 2 - Drain  
3 - Source

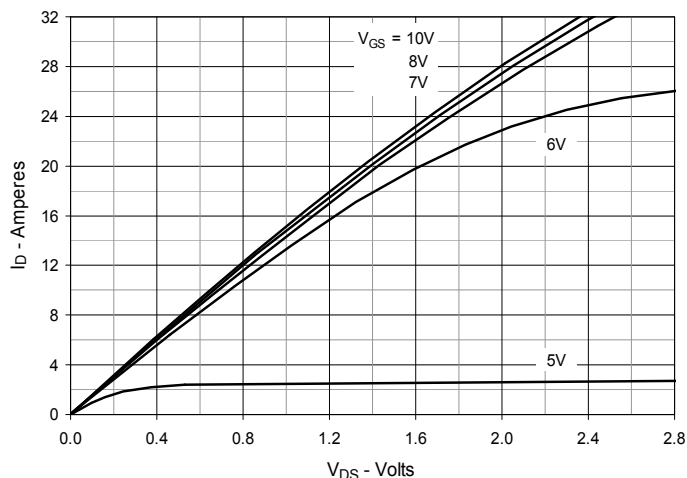
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

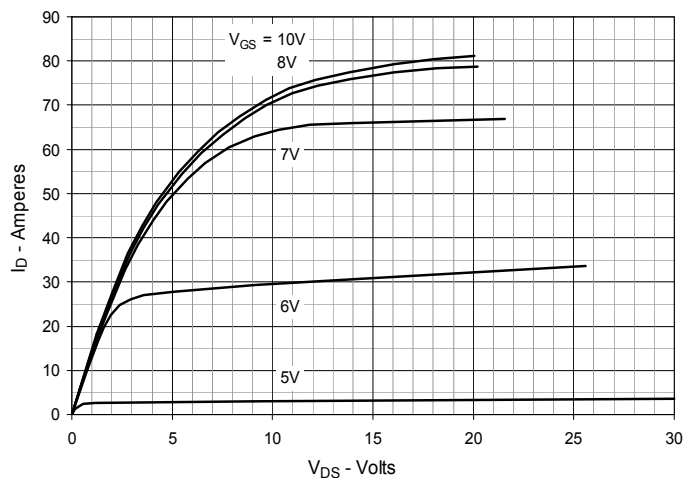
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

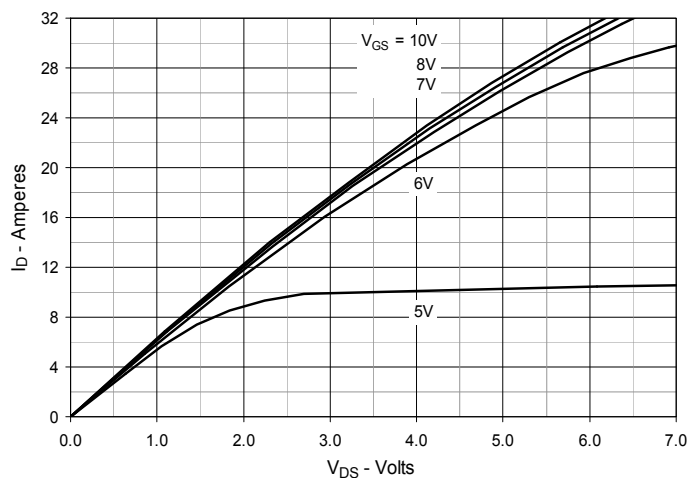
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



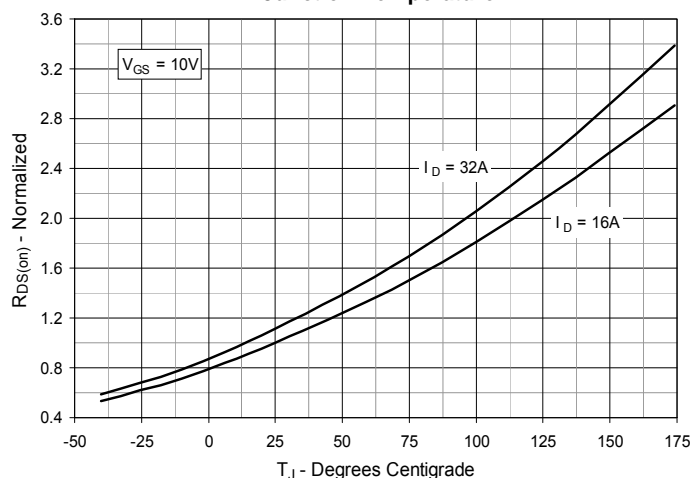
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



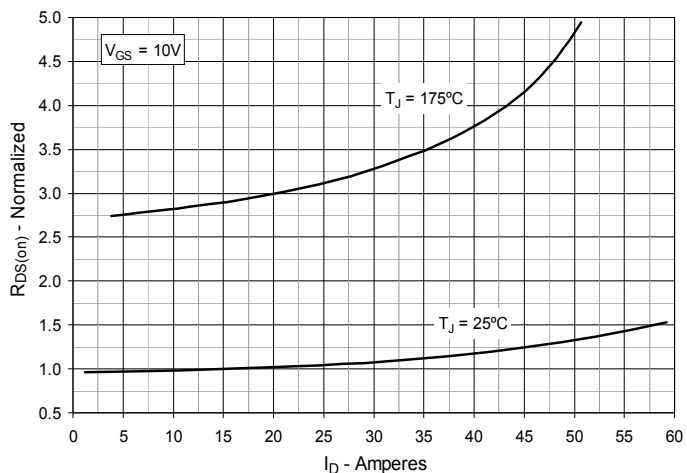
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



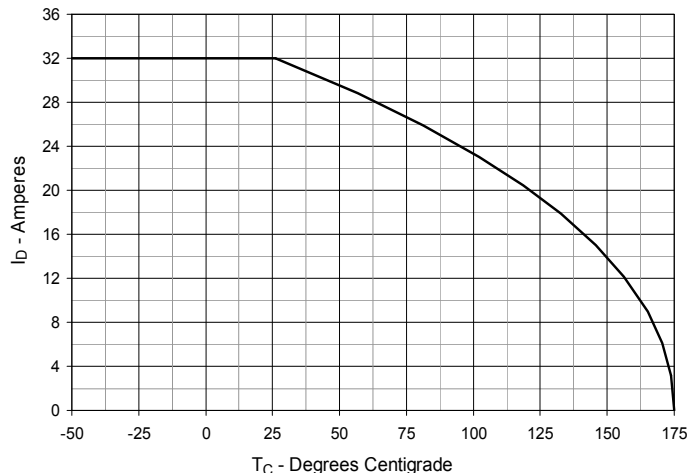
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 16A$  Value vs. Junction Temperature**



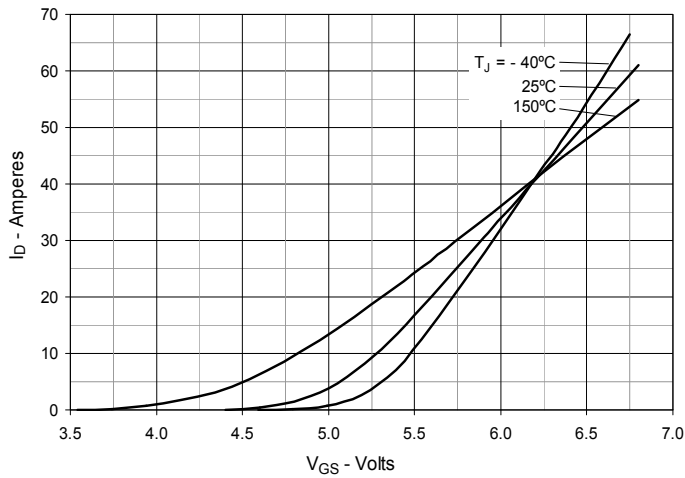
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 16A$  Value vs. Drain Current**



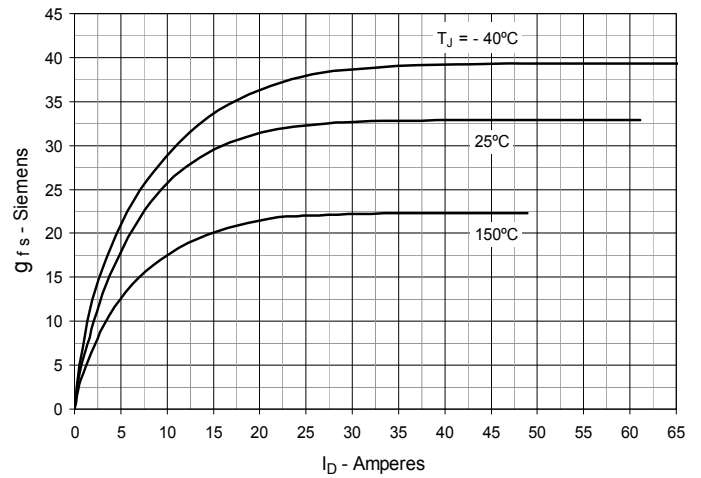
**Fig. 6. Drain Current vs. Case Temperature**



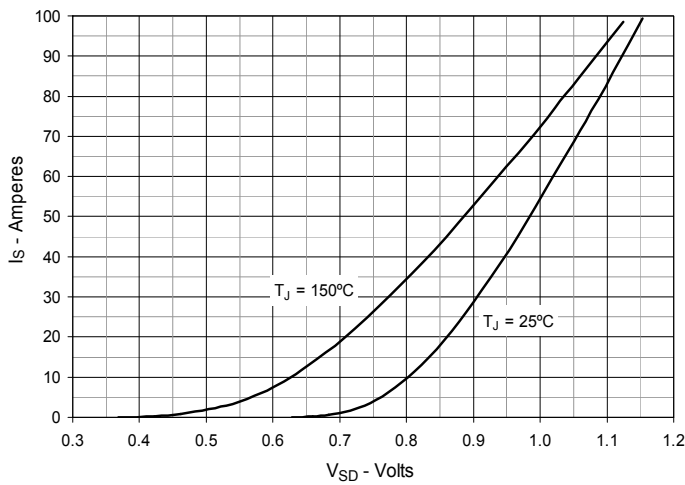
**Fig. 7. Input Admittance**



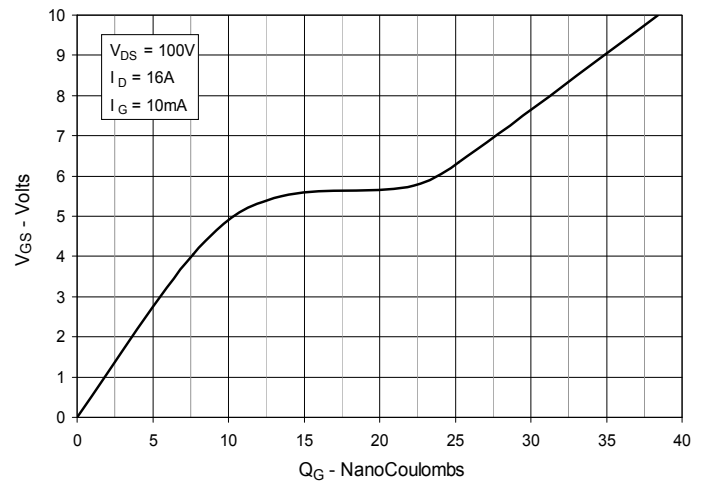
**Fig. 8. Transconductance**



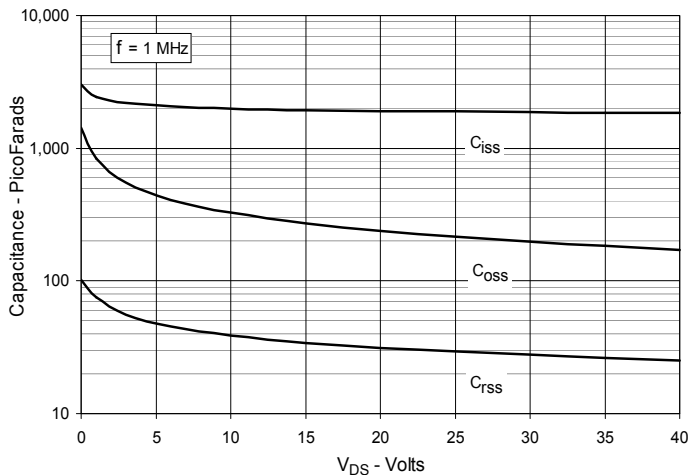
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



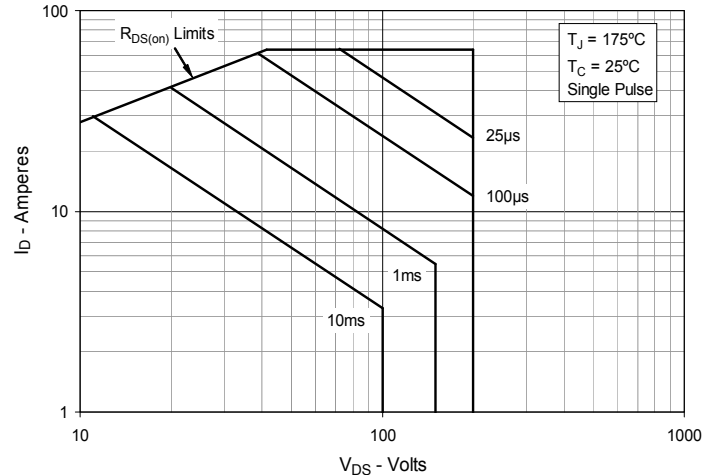
**Fig. 10. Gate Charge**



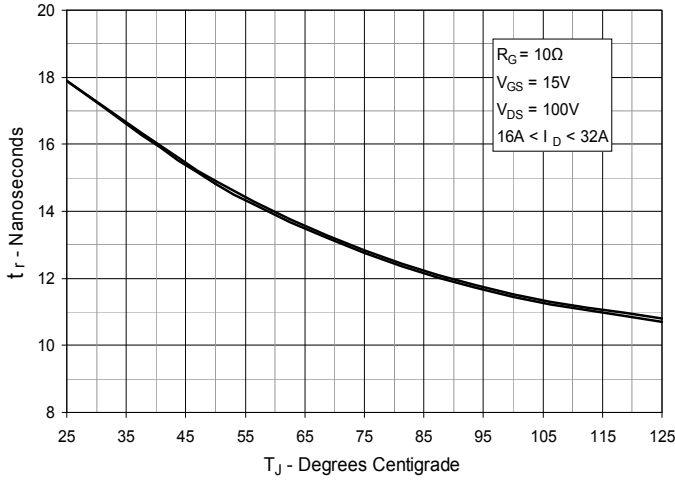
**Fig. 11. Capacitance**



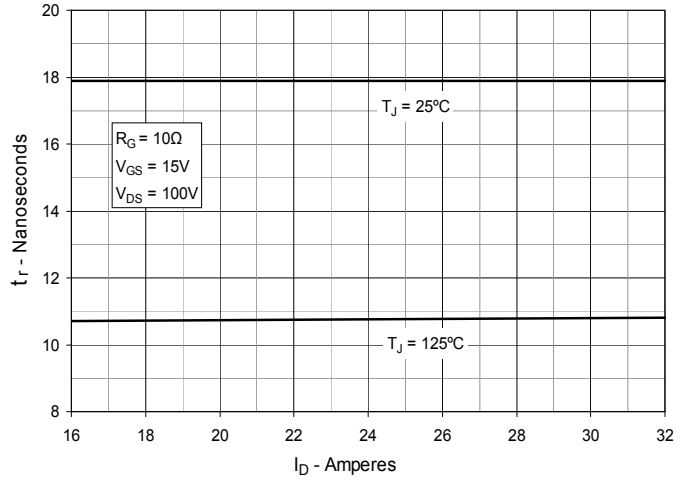
**Fig. 12. Forward-Bias Safe Operating Area**



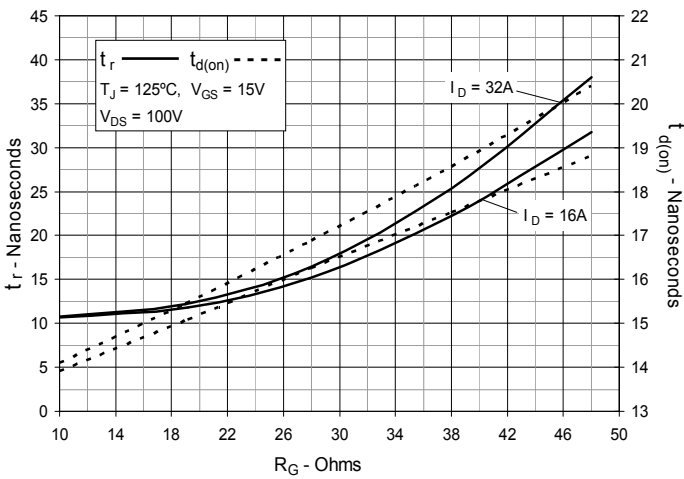
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



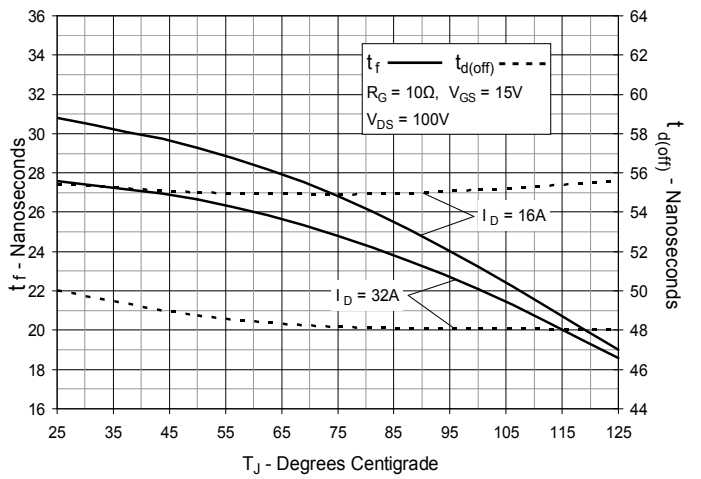
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



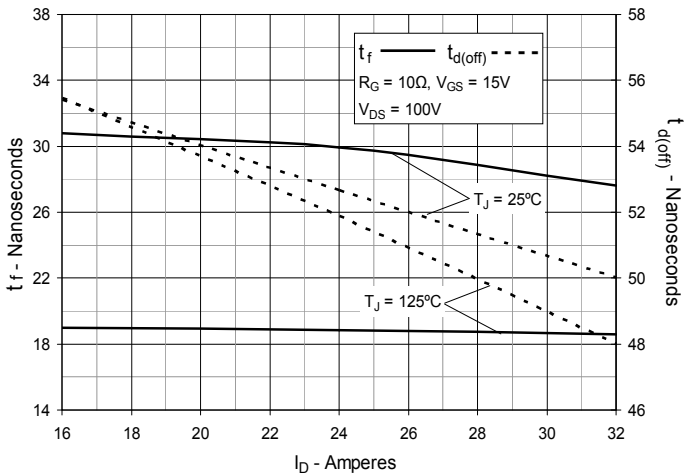
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



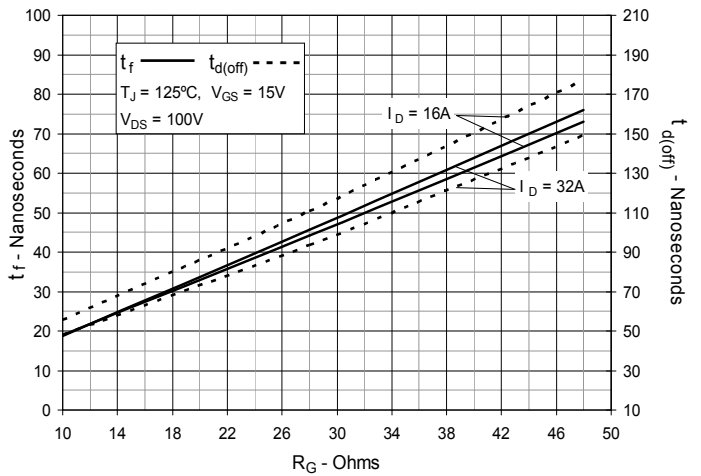
**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**



**Fig. 19. Maximum Transient Thermal Impedance**

